

Case study of IBIS V4.1 by JEITA EDA-WG

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**JEITA EDA-WG
A. Itoh, T. Watanabe, N. Matsui**

JEITA ; Japan Electronics and Information Technology Industries Association

Outlines

- 1. JEITA EDA-WG Activities**
- 2. Case study of IBIS V4.1**
- 3. EMI Model**

1. JEITA EDA-WG Activities

Objectives of JEITA EDA

EDA Model for

Digital Consumer Electronics

**Cellular Phone, LCD TV, Digital Camera/Video,
DVD Recorder**

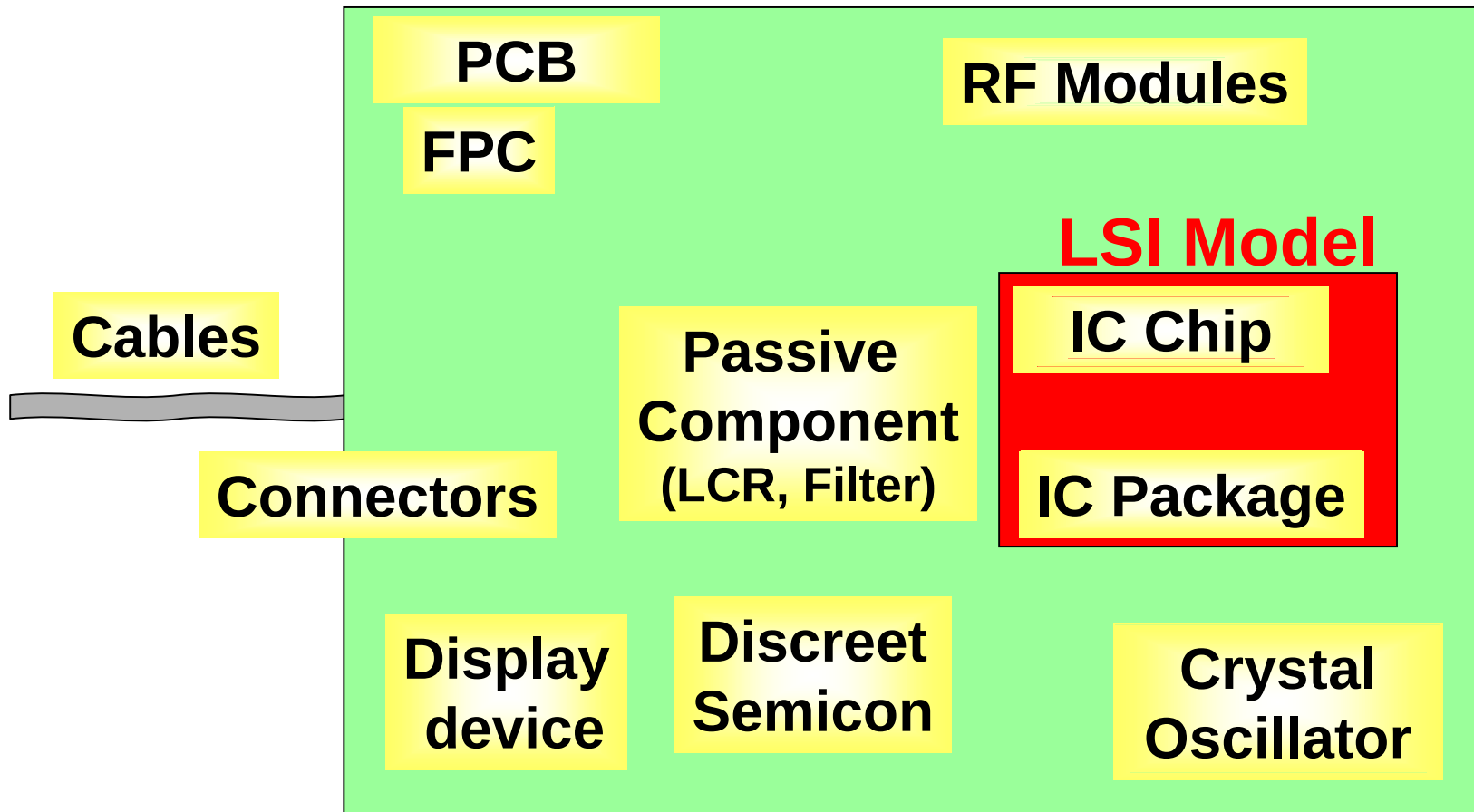
(Digital , RF, and Analog circuits)

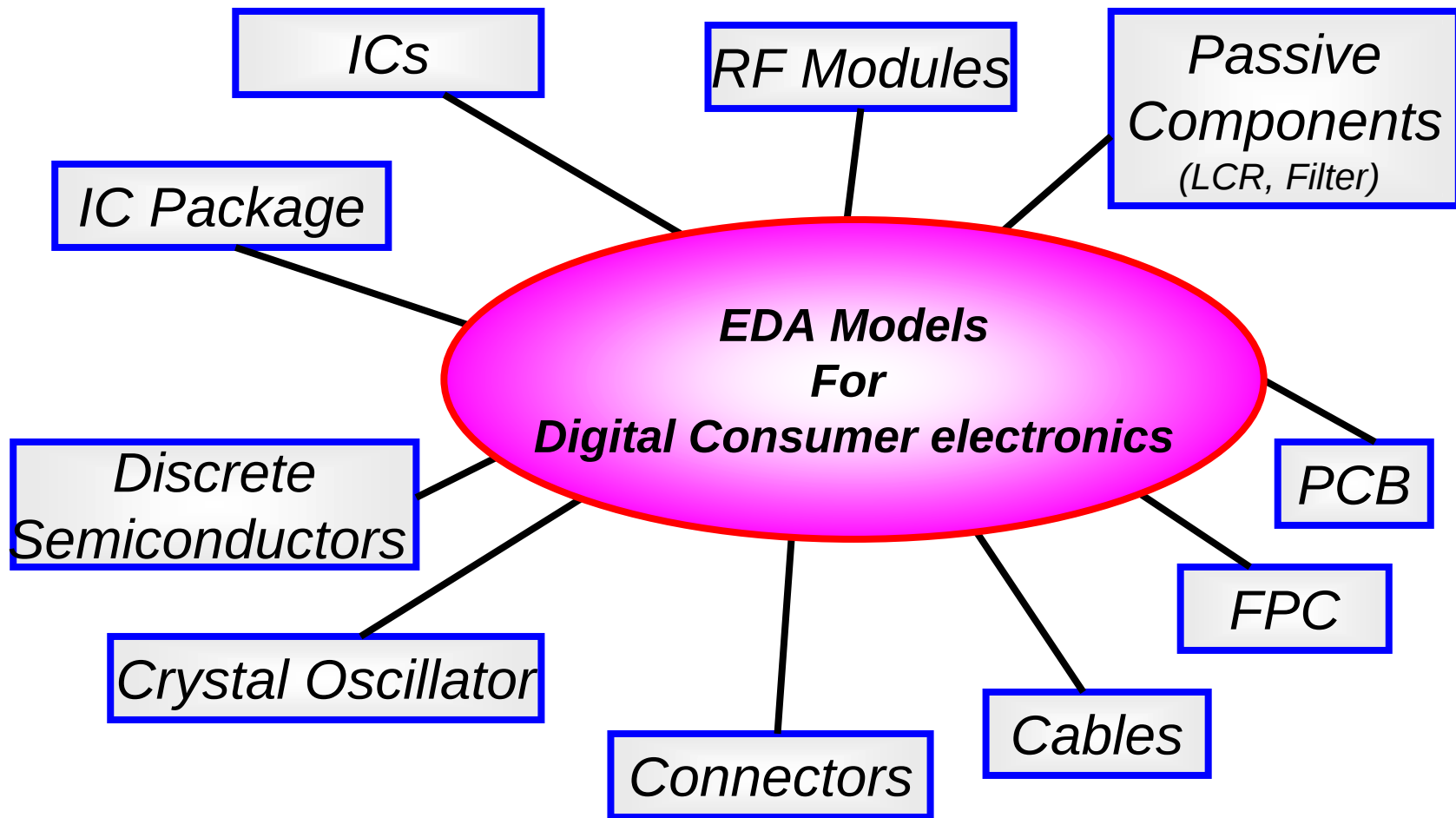
Auto Mobile Electronics ?

(Motor Drive, EMC)

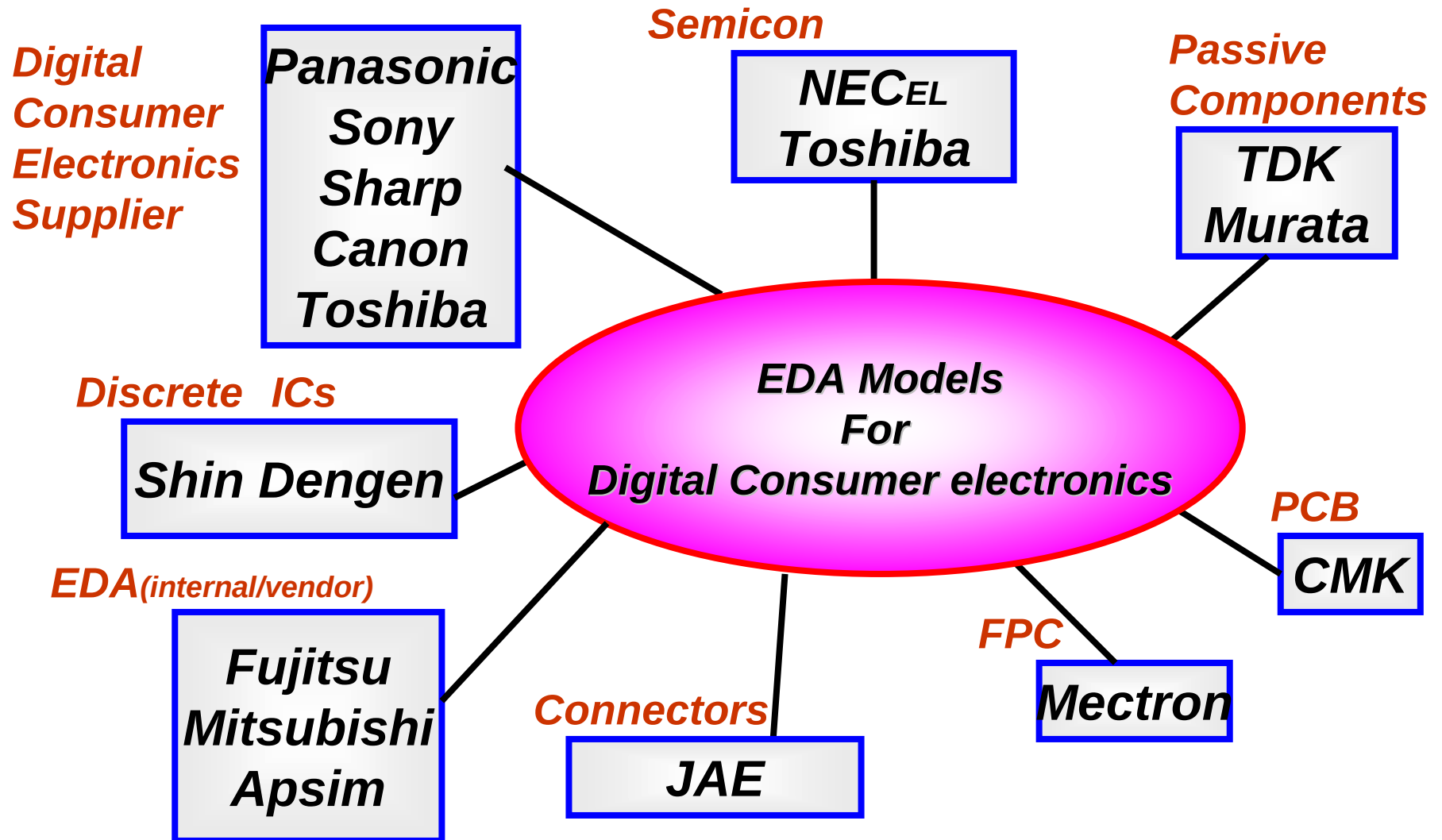
< Applicability of IBIS V4.1 >

EDA Model for SI, PI and EMI Simulation





JEITA EDA-WG Member

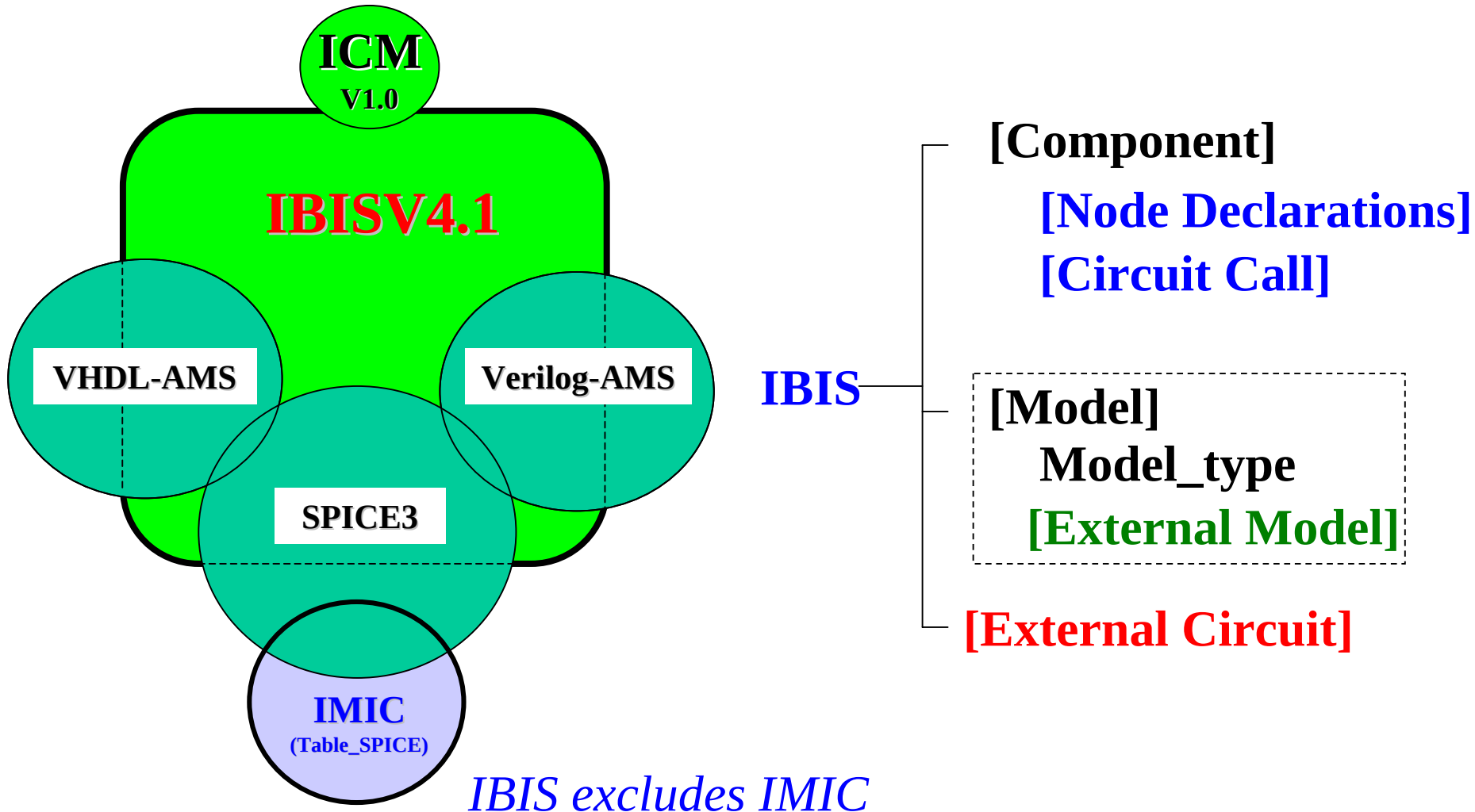


2. Case study of IBIS V4.1

Summary of investigation of IBIS V4.1

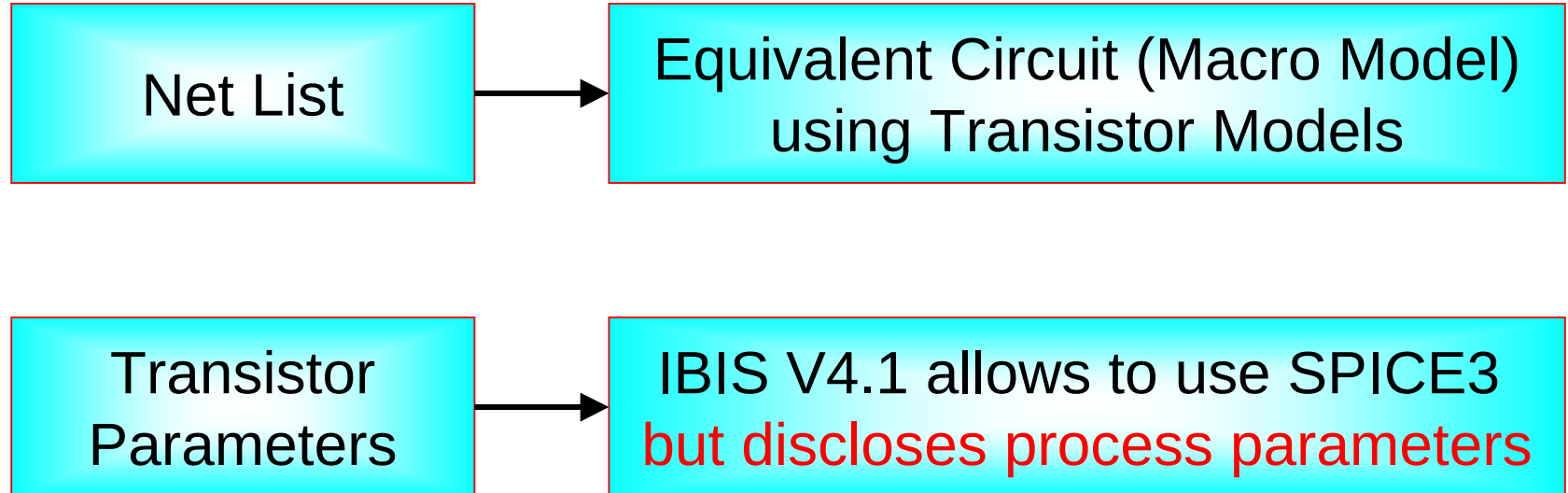
	IBIS				Comments
	V3.2	V4.1 SPICE	V4.1 *AMS	ICM	
ASIC/SOC for EMI/SSO		✓	(✓)		Accurate models need the internal gates for EMI/SSO. IBIS V4.1 SPICE discloses process parameters.
Power Semiconductor OpAMP		✓	(✓)		IBIS V4.1 SPICE discloses process parameters.
DSP, AD/DA, Xtal	✓	✓	✓		I/O for SI can be described in V3.2. Inside needs *AMS.
Passive Components	(✓)	✓	(✓?)	✓	Can describe LCRK models ICM describes S-parameters
Package, Module, PCB	(✓)	✓	(✓?)	✓	IBIS 4.1 SPICE can't describe S-parameters or lossy coupled transmission line. ICM can't include discrete components. SiP and PWRGND modeling.
Connector, Cable, FPC		(✓)	(✓)	✓	ICM can't include discrete components.

Understanding of IBIS V4.1



How to describe SPICE transistor model in IBIS 4.1 without disclosing proprietary information

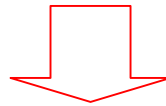
Models described in SPICE transistors have flexibility.



IMIC (Table_SPICE) allows to hide the transistor parameters, but IBIS V4.1 excludes IMIC.

How to hide transistor model parameters in IBIS V4.1 SPICE description without losing accuracy

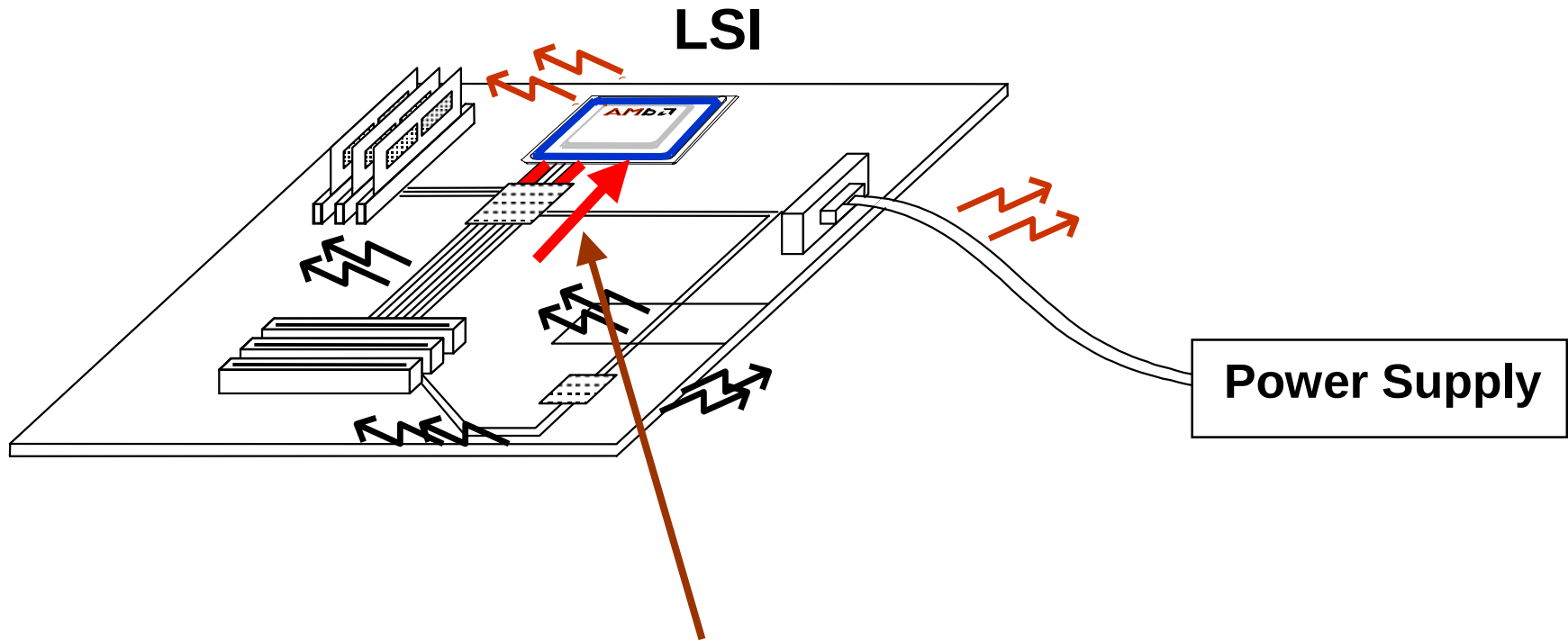
IMIC (Table_SPICE) allows to hide the transistor parameters, but IBIS V4.1 excludes IMIC.



Need to have a bridge from IMIC to IBIS V4.1 SPICE 3 without disclosing the original SPICE transistor parameters.

3. EMI Model (NEC/APSIM)

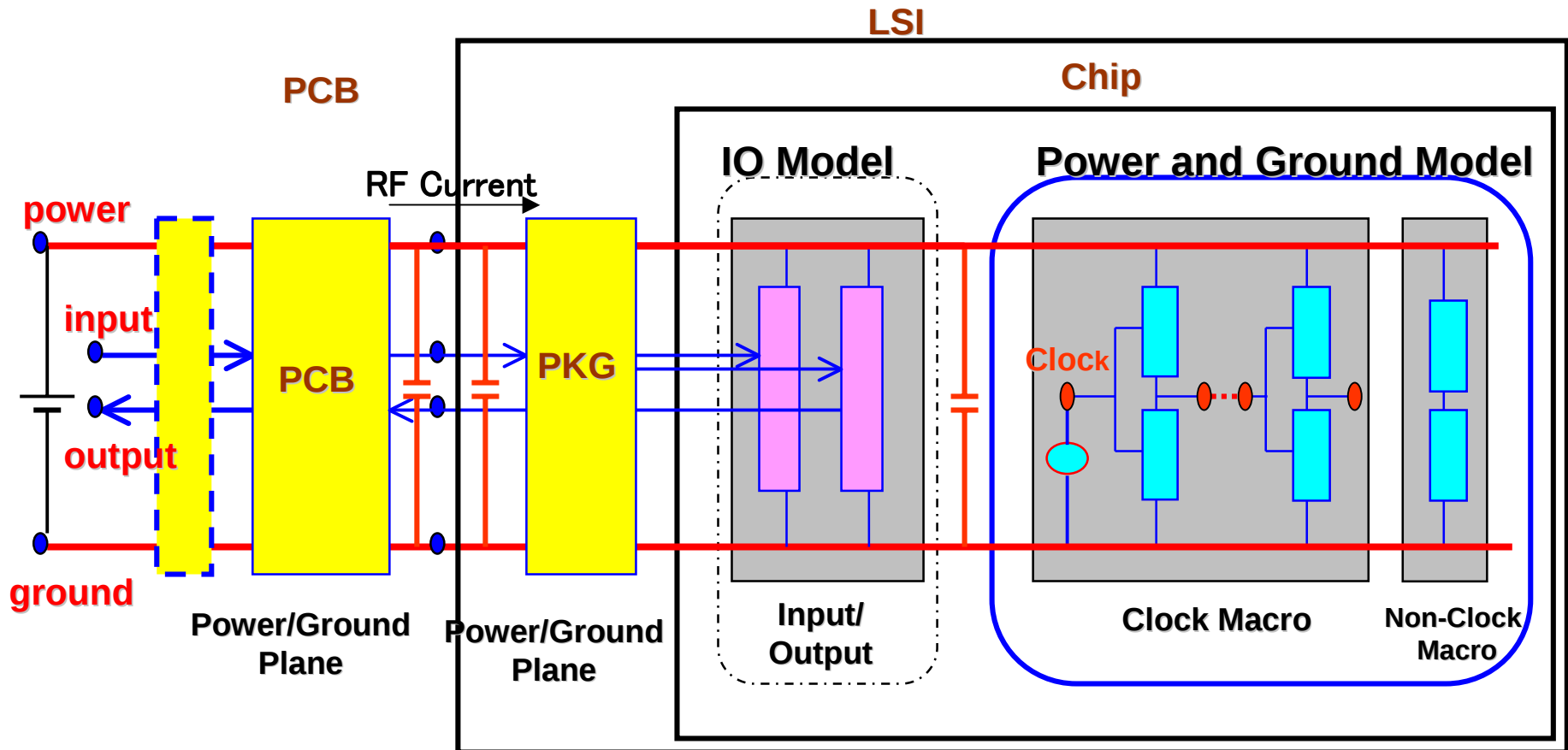
LSI Model for EMI Simulation



RF Current of LSI

1. Measurement; IEC61967-6.Magnetic Probe Method
2. Simulation Model; EMI Model for LSI

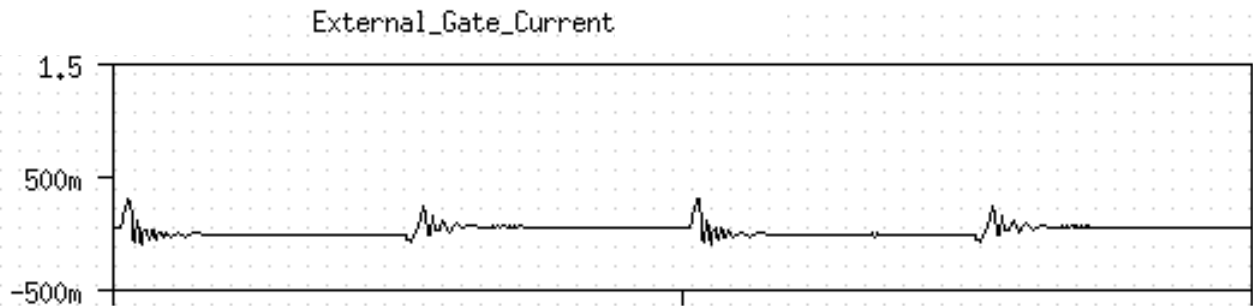
EMI Simulation for PCB



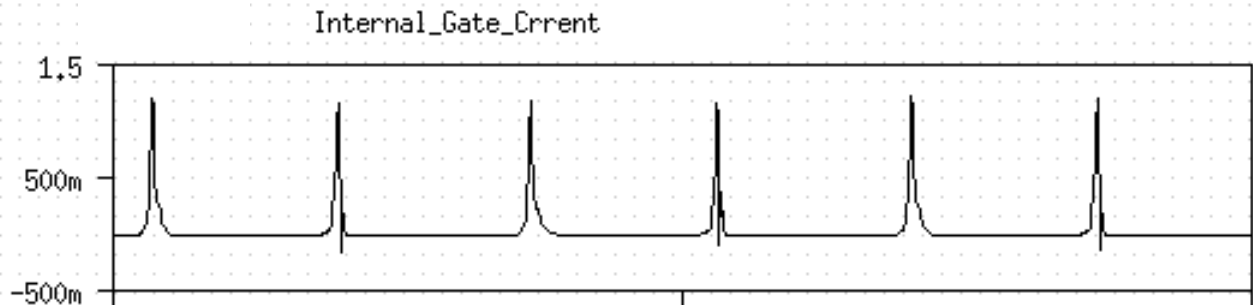
EMI simulation needs the internal gates power/ground model with loading effects in time/frequency domain.

Current Waveforms of 32-bit LSI

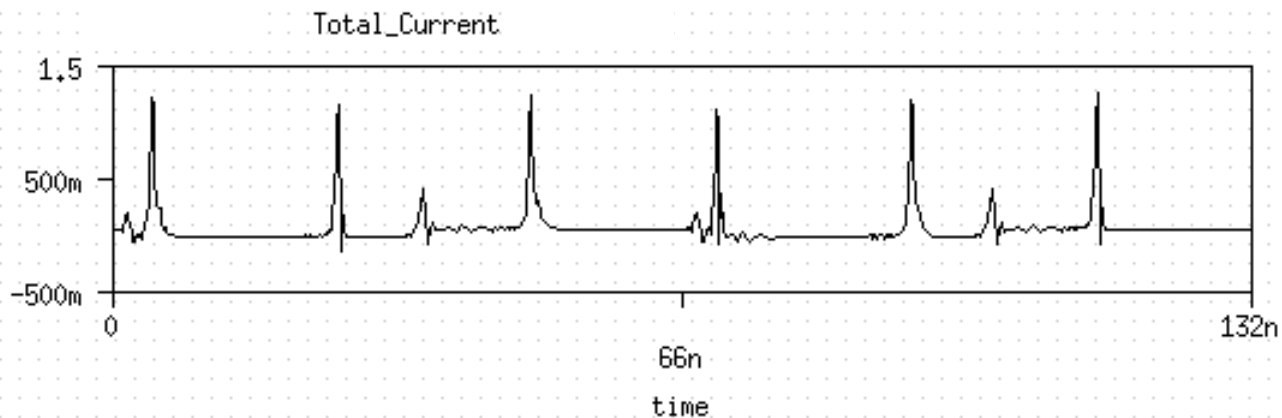
Output



Internal

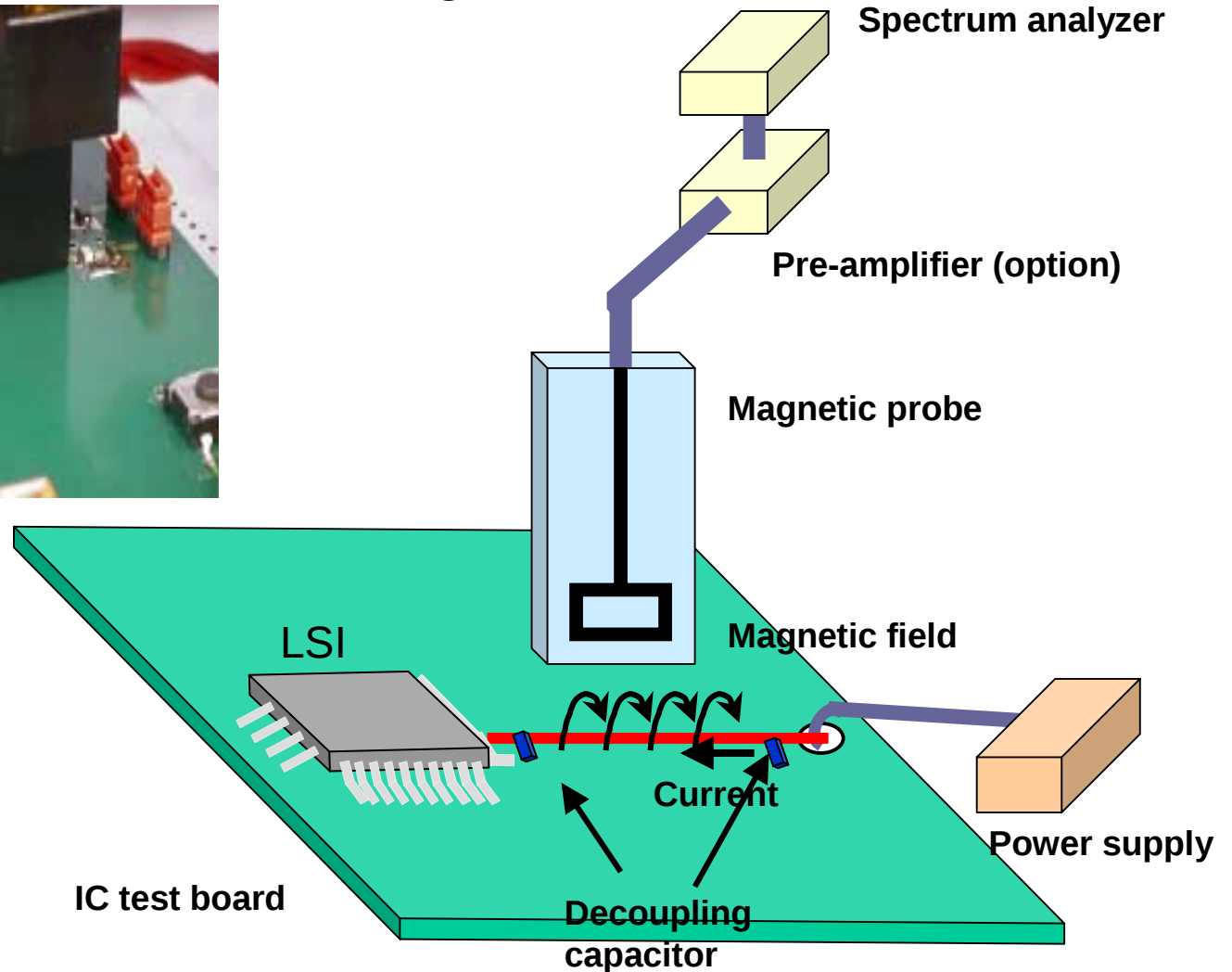
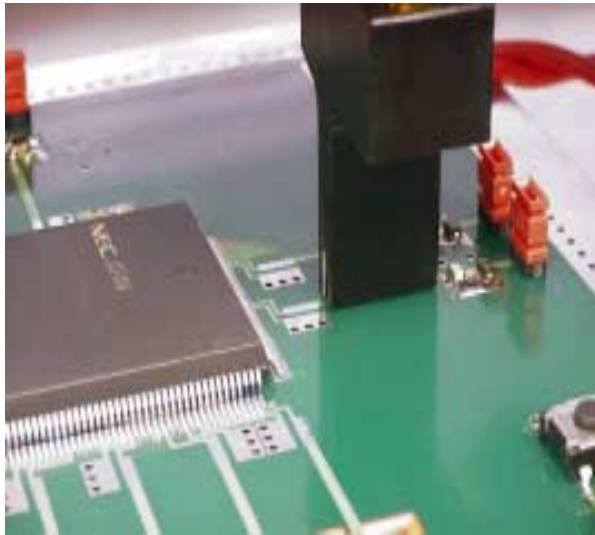


Total

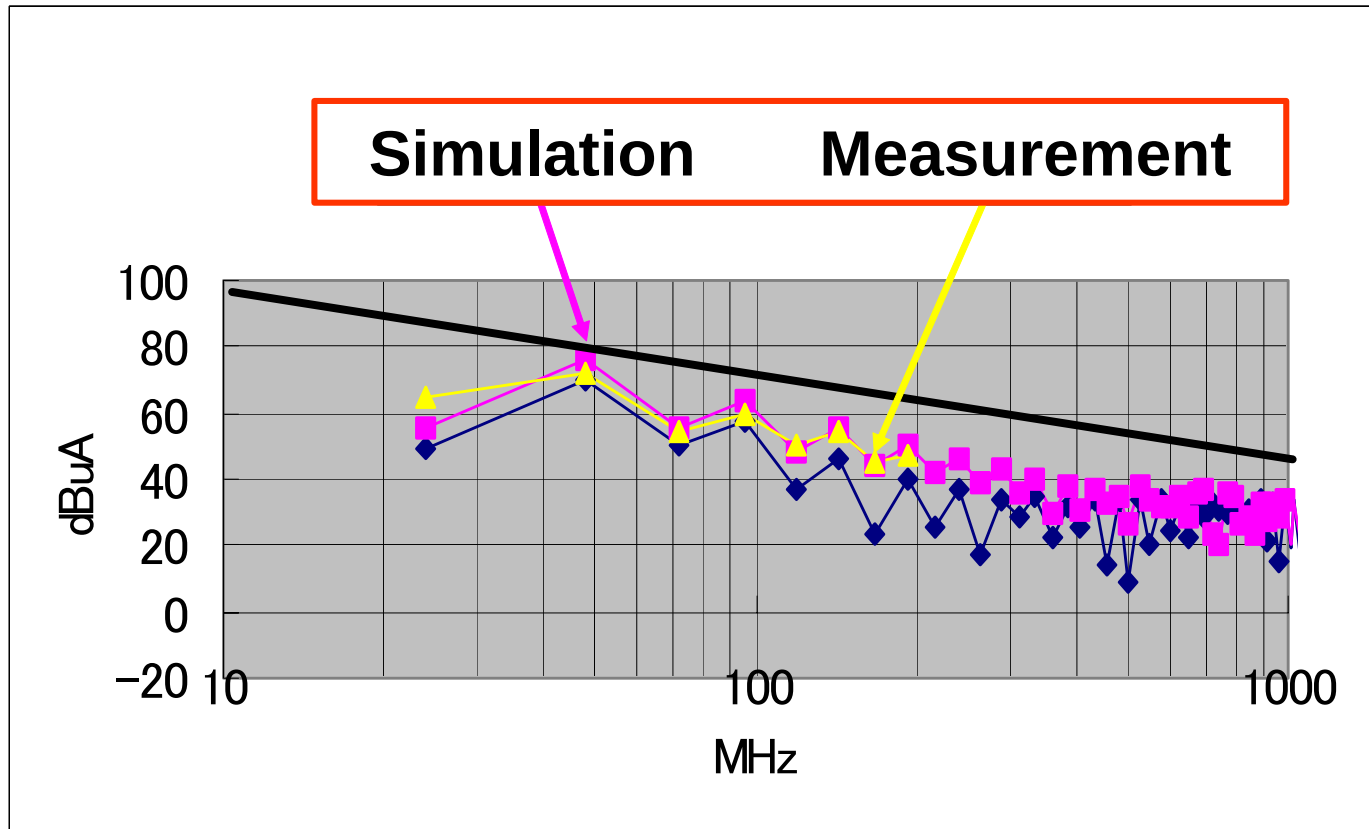


Measurement

IEC61967-6. Magnetic Probe Method

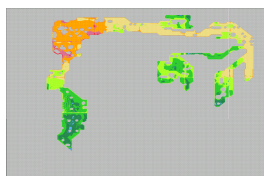
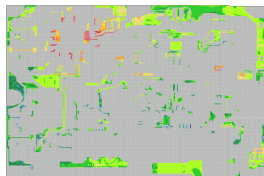
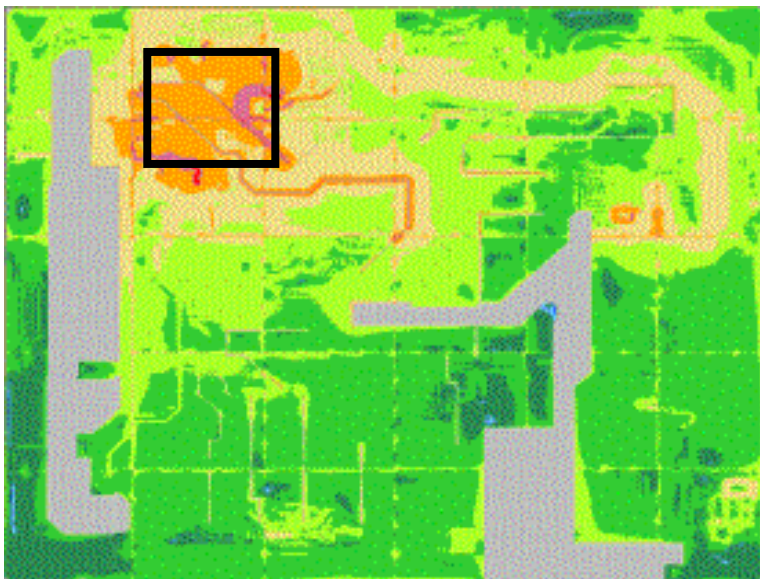


Simulation VS Measurement

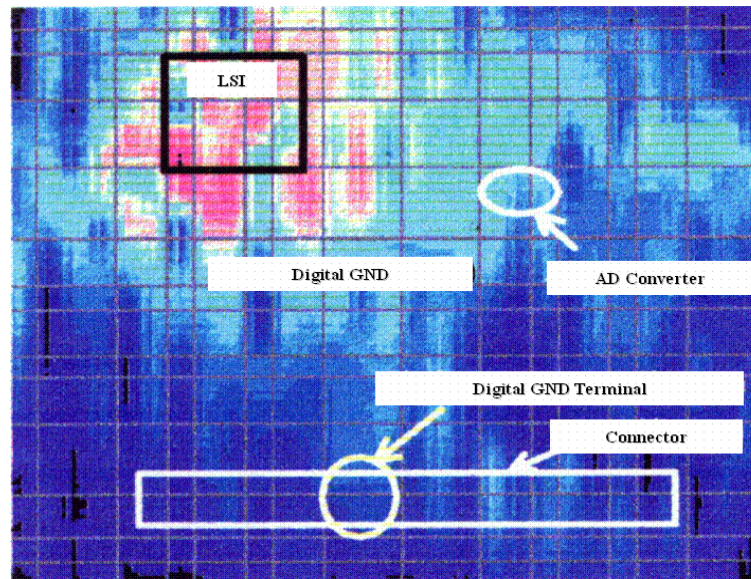


Current/Magnetic Field Distribution

Simulation



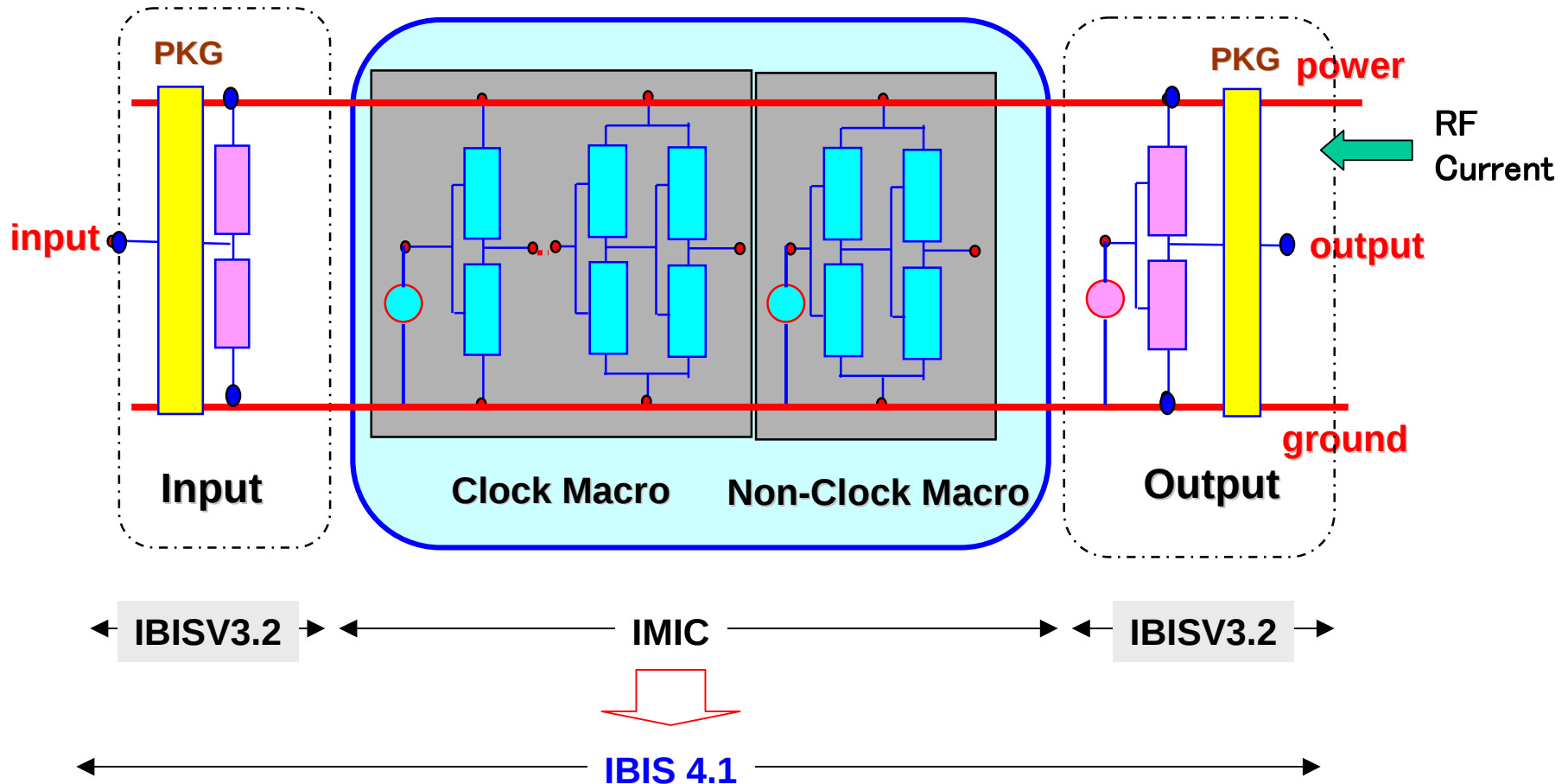
Measurement



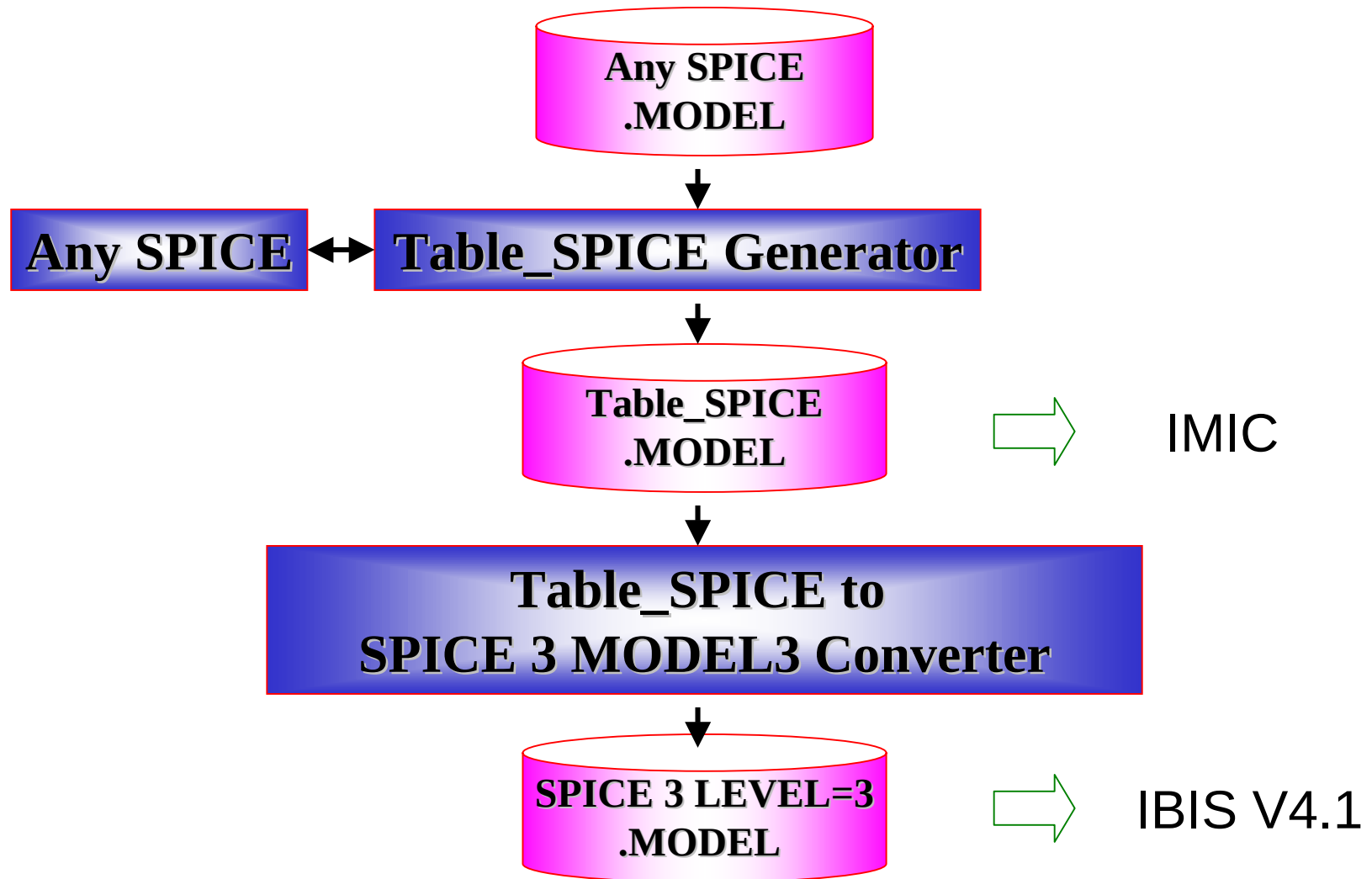
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EMI Simulation Model for LSI

Power and Ground Model of Core Logics (internal gates)

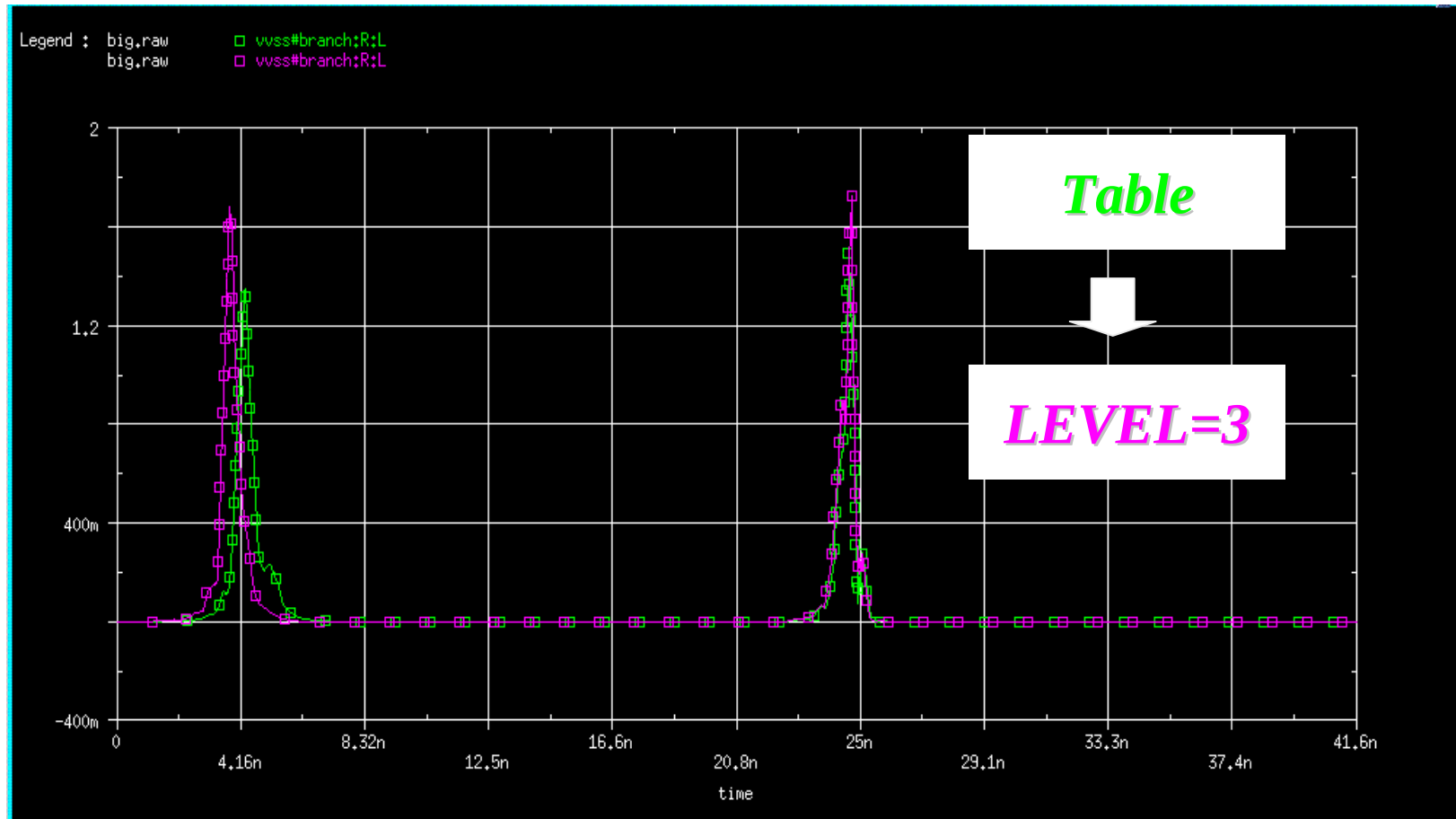


Developed IMIC to IBIS V4.1 Converter



The parameters of LEVEL=3 can't disclose those of the original SPICE.

Full chip power/ground current models in time/frequency domain for EMI Simulation



Example of LSI Power/Ground Model (IBIS V 4.1)

Apsim LSI Power and Ground model ckt file

* Command: ApsimLPG 1.400.5

* File: big.ckt

* Pre - Driver Model

xPRDRV.in PreVDD PreVSS PreIN PreMID PRDRV.in

xPRDRV.out PreVDD PreVSS PreMID PreOUT PRDRV.out

vvdd1 PreVDD 0 dc 3.3

vvss1 PreVSS 0 dc 0.0

xshort1 PreOUT D2P_N0039026 D2P_N0000004 D2P_N0000003 D2P_N0000002 D2P_N0000001 short1

* Clock - Driver Model

cD2P_N0039026_1 D2P_N0039026 VDD 2.192774e-013

cD2P_N0039026_2 D2P_N0039026 VSS 2.192774e-013

xD2P_I0033331.in VDD VSS D2P_N0039026 mid_D2P_I0033331 F111.in

xD2P_I0033331.out VDD VSS mid_D2P_I0033331 D2P_N0029114 F111.out

cD2P_N0029114_1 D2P_N0029114 VDD 5.332500e-016

cD2P_N0029114_2 D2P_N0029114 VSS 5.332500e-016

xD2P_I0033330.in VDD VSS D2P_N0029114 mid_D2P_I0033330 F111.in

xD2P_I0033330.out VDD VSS mid_D2P_I0033330 D2P_N0028992 F111.out

cD2P_N0028992_1 D2P_N0028992 VDD 3.680150e-015

cD2P_N0028992_2 D2P_N0028992 VSS 3.680150e-015

xD2P_I0033329.in VDD VSS D2P_N0028992 mid_D2P_I0033329 F111.in

xD2P_I0033329.out VDD VSS mid_D2P_I0033329 D2P_N0028991 F111.out

cD2P_N0028991_1 D2P_N0028991 VDD 8.436000e-016

cD2P_N0028991_2 D2P_N0028991 VSS 8.436000e-016

xFF1.in VDD VSS D2P_N0000092 FF1_mid FF1.in
xFF1.out VDD VSS FF1_mid FF1_out FF1.out
rFF1.out FF1_out 0 100meg

* Non-Clock Model

*xnc VDD VSS NCFF

xnc VDD VSS NCCR

* Voltage source

vvdd VDD 0 dc 3.3

vvss VSS 0 dc 0.0

* Open Nodes

Ropen1 node_open1 0 100Meg

* Include file

.include big.tst

.include mos_tsp.lib

*.include spice.lib

.include big.sckt

* Save current

.save vvdd#branch vvss#branch

.end

Example of LSI Power/Ground Model (IBIS V 4.1)

① Original SPICE MOS parameters

```
.MODEL NENH NMOS
+ LEVEL = TOX =
+ LMIN = PHI =
+ VFB = GAMMA =
+ VDOP = CDOP =
```

② Table_SPICE MOS V-I-C data

```
.model NENH nmos model=table
+ l=0.25u w=2u pd=5e-6 ps=5e-6 ad=0.5e-12 as=0.5e-12
+ nolimiting
+ data=channel
+ points=1326
+ grid=yes
+ vbs = 0.000e+00
* Vgs Vds Ids Cgs Cgd Cgb
*
+ 0.000e+00 0.000e+00 0.000e+00 2.093e-16 2.093e-16 2.763e-16
+ 0.000e+00 1.000e-01 1.821e-12 2.093e-16 2.093e-16 2.749e-16
+ 0.000e+00 2.000e-01 2.039e-12 2.093e-16 2.093e-16 2.734e-16
+ 0.000e+00 3.000e-01 2.240e-12 2.093e-16 2.093e-16 2.720e-16
+ 0.000e+00 4.000e-01 2.460e-12 2.093e-16 2.093e-16 2.706e-16
+ 0.000e+00 5.000e-01 2.704e-12 2.093e-16 2.093e-16 2.691e-16
+ 0.000e+00 6.000e-01 2.973e-12 2.093e-16 2.093e-16 2.677e-16
```

③ SPICE 3 Level=3 MOS minimum parameters

```
.model NENH nmos level = 3 tox = 1.11102e-08 phi = 0.6
+ vt0 = 0.631419 kp = 1.31264e+09 theta = 8.18536e+12
+ vmax = 196589 u0 = 4.22341e+15
+ js = 2.0364e-06 - - - - -
```